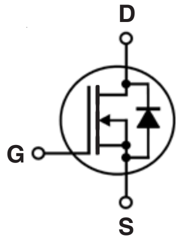
IXYS

Depletion Mode MOSFET

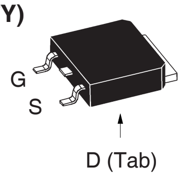
IXTY1R6N50D2
IXTA1R6N50D2
IXTP1R6N50D2

V_{DSX} = 500V
$I_{D(on)}$ ≥ 1.6A
$R_{DS(on)}$ ≤ 2.3Ω

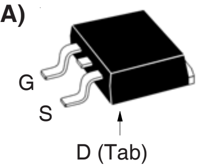
N-Channel



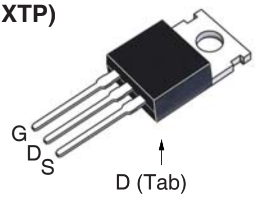
TO-252 (IXTY)



TO-263 (IXTA)



TO-220 (IXTP)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSX}	T_J = 25°C to 150°C	500	V
V_{GSX}	Continuous	±20	V
V_{GSM}	Transient	±30	V
P_D	T_C = 25°C	100	W
T_J		- 55 ... +150	°C
T_{JM}		150	°C
T_{stg}		- 55 ... +150	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
M_d	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-252	0.35	g
	TO-263	2.50	g
	TO-220	3.00	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSX}	V_{GS} = - 5V, I_D = 250µA	500			V
$V_{GS(off)}$	V_{DS} = 25V, I_D = 100µA	- 2.5		- 4.5	V
I_{GSX}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
$I_{DSX(off)}$	V_{DS} = V_{DSX}, V_{GS} = - 5V			2	µA
	T_J = 125°C			25	µA
$R_{DS(on)}$	V_{GS} = 0V, I_D = 0.8A, Note 1			2.3	Ω
$I_{D(on)}$	V_{GS} = 0V, V_{DS} = 25V, Note 1	1.6			A

Features

- Normally ON Mode
- International Standard Packages
- Molding Epoxies Meet UL 94 V-0 Flammability Classification

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Audio Amplifiers
- Start-up Circuits
- Protection Circuits
- Ramp Generators
- Current Regulators
- Active Loads

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	 Typ.	 Max.	
g_{fs}	V_{DS} = 30V, I_D = 0.8A, Note 1	1.00	1.75		S
C_{iss}	V_{GS} = -10V, V_{DS} = 25V, f = 1MHz		645		pF
C_{oss}			65		pF
C_{rss}			16.5		pF
$t_{d(on)}$	**Resistive Switching Times** V_{GS} = ±5V, V_{DS} = 250V, I_D = 0.8A R_G = 5Ω (External)		25		ns
t_r			70		ns
$t_{d(off)}$			35		ns
t_f			41		ns
$Q_{g(on)}$	V_{GS} = 5V, V_{DS} = 250V, I_D = 0.8A		23.7		nC
Q_{gs}			2.2		nC
Q_{gd}			13.8		nC
R_{thJC}				1.25	°C/W
R_{thCS}	TO-220		0.50		°C/W

Safe-Operating-Area Specification

Symbol	Test Conditions	Characteristic Values Min.	 Typ.	 Max.	
SOA	V_{DS} = 400V, I_D = 0.15A, T_C = 75°C, Tp = 5s	60			W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	 Typ.	 Max.	
V_{SD}	I_F = 1.6A, V_{GS} = -10V, Note 1		0.8	1.3	V
t_{rr}	I_F = 1.6A, -di/dt = 100A/μs V_R = 100V, V_{GS} = -10V		400		ns
I_{RM}			9.16		A
Q_{RM}			1.83		μC

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

Fig. 1. Output Characteristics @ $T_J = 25^oC$

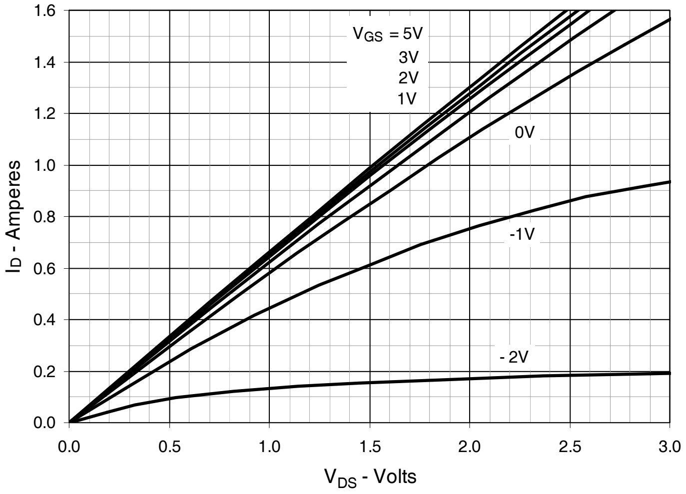


Fig. 2. Extended Output Characteristics @ $T_J = 25^oC$

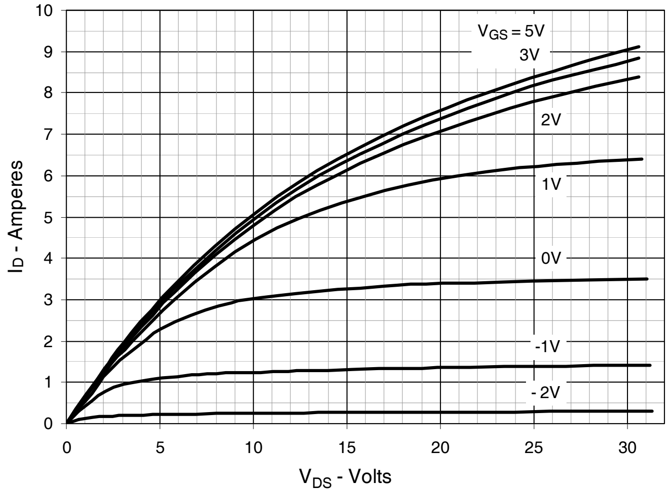


Fig. 3. Output Characteristics @ $T_J = 125^oC$

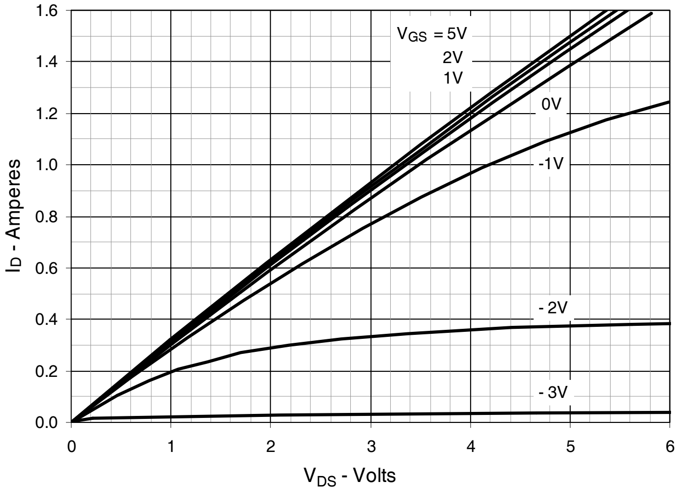


Fig. 4. Drain Current @ $T_J = 25^oC$

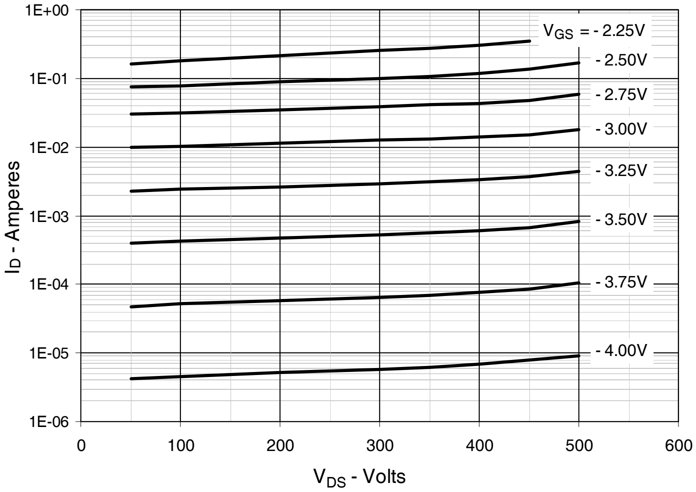


Fig. 5. Drain Current @ $T_J = 100^oC$

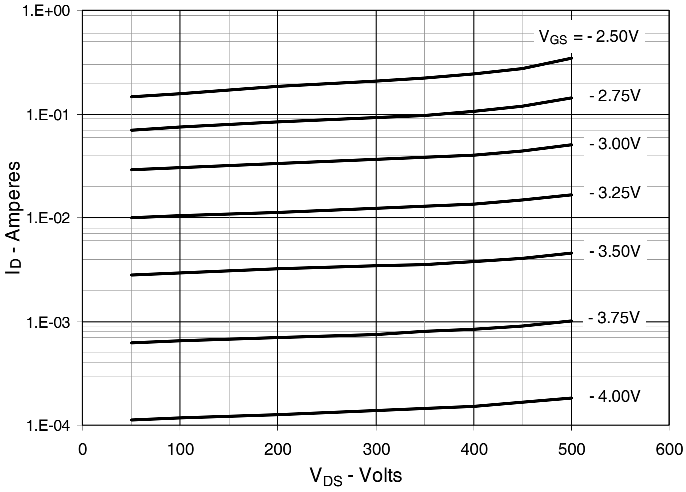


Fig. 6. Dynamic Resistance vs. Gate Voltage

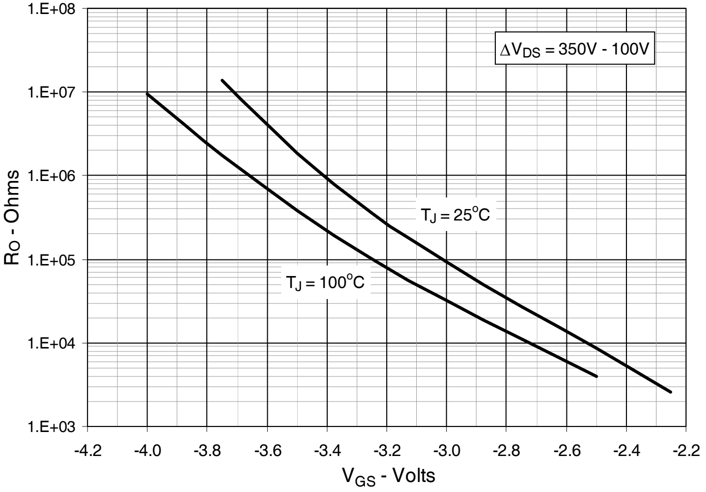


Fig. 7. Normalized $R_{DS(on)}$ vs. Junction Temperature

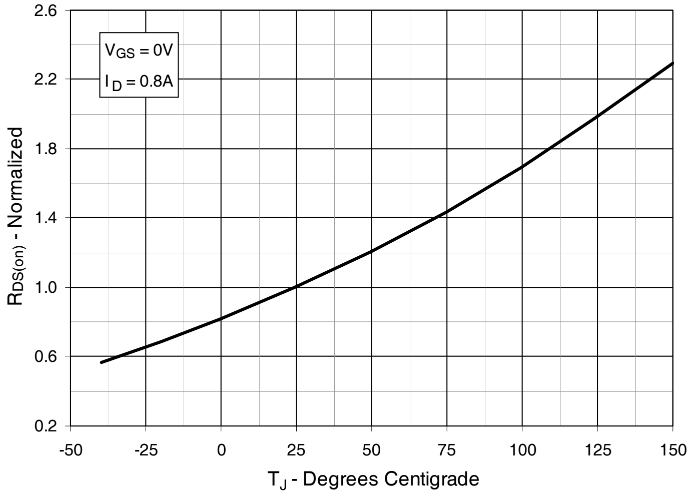


Fig. 8. $R_{DS(on)}$ Normalized to I_D = 0.8A Value vs. Drain Current

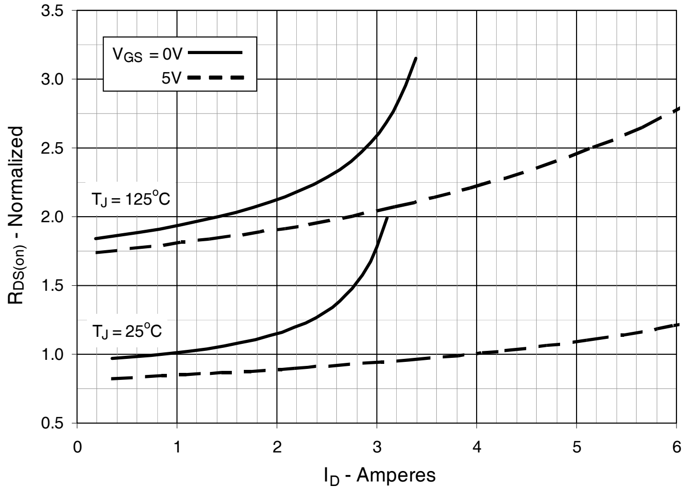


Fig. 9. Input Admittance

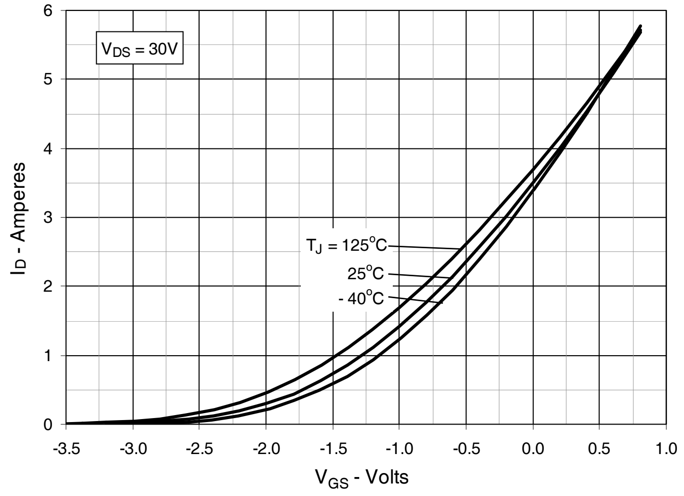


Fig. 10. Transconductance

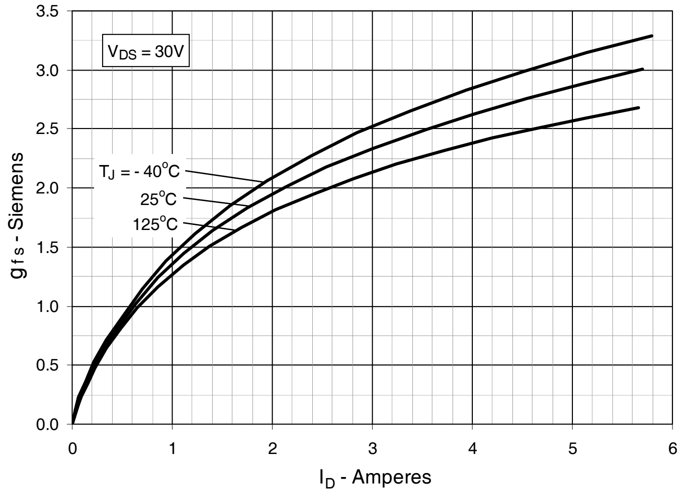


Fig. 11. Breakdown and Threshold Voltages vs. Junction Temperature

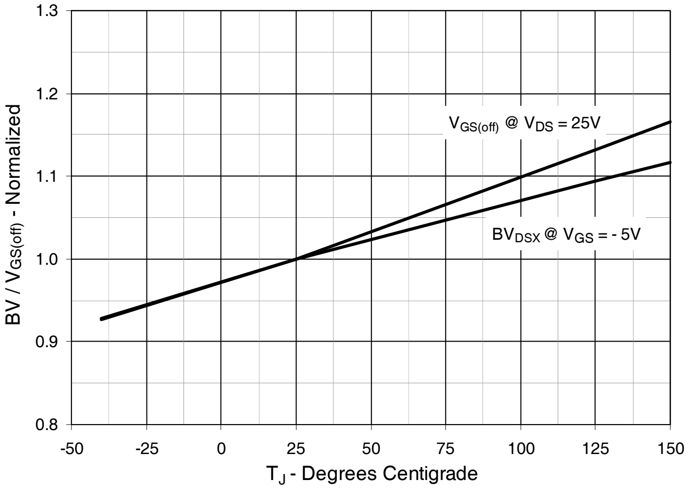


Fig. 12. Forward Voltage Drop of Intrinsic Diode

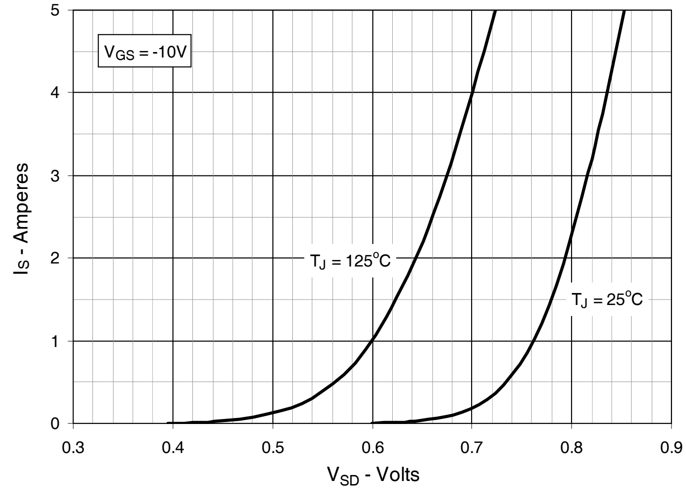


Fig. 13. Capacitance

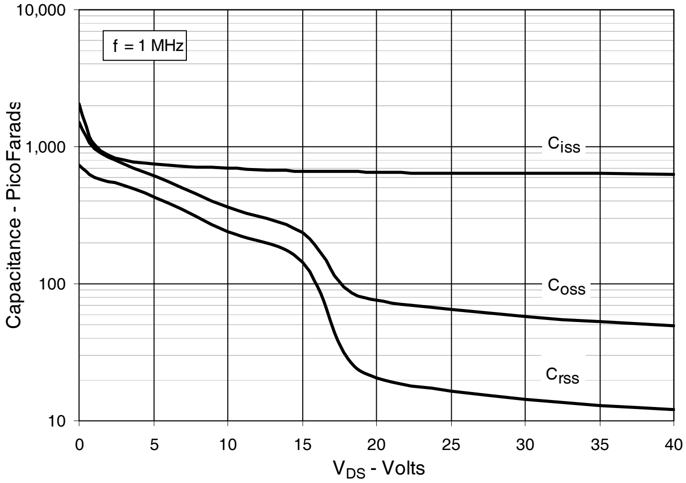


Fig. 14. Gate Charge

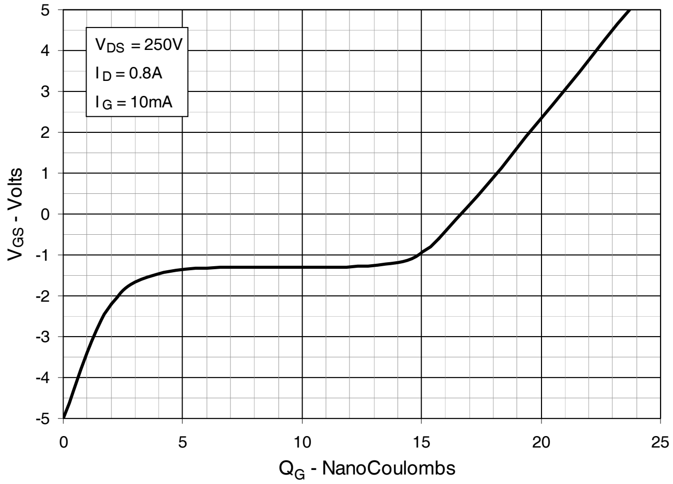


Fig. 15. Forward-Bias Safe Operating Area @ T_C = 25°C

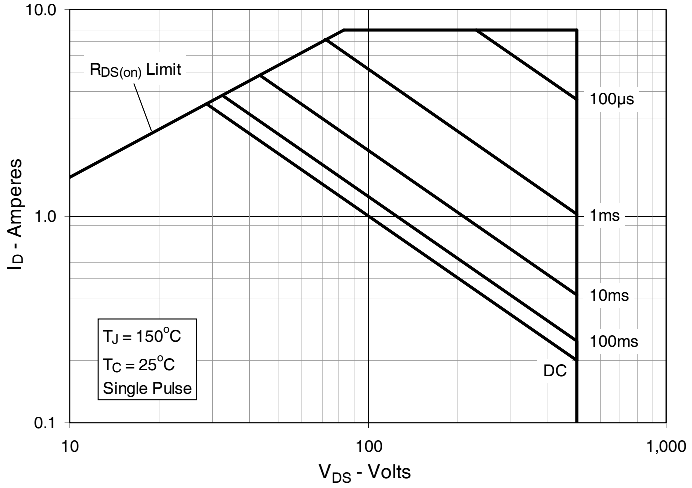


Fig. 16. Forward-Bias Safe Operating Area @ T_C = 75°C

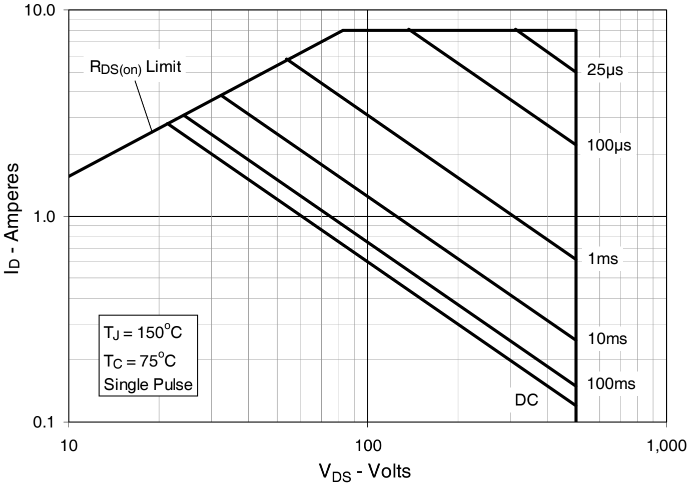
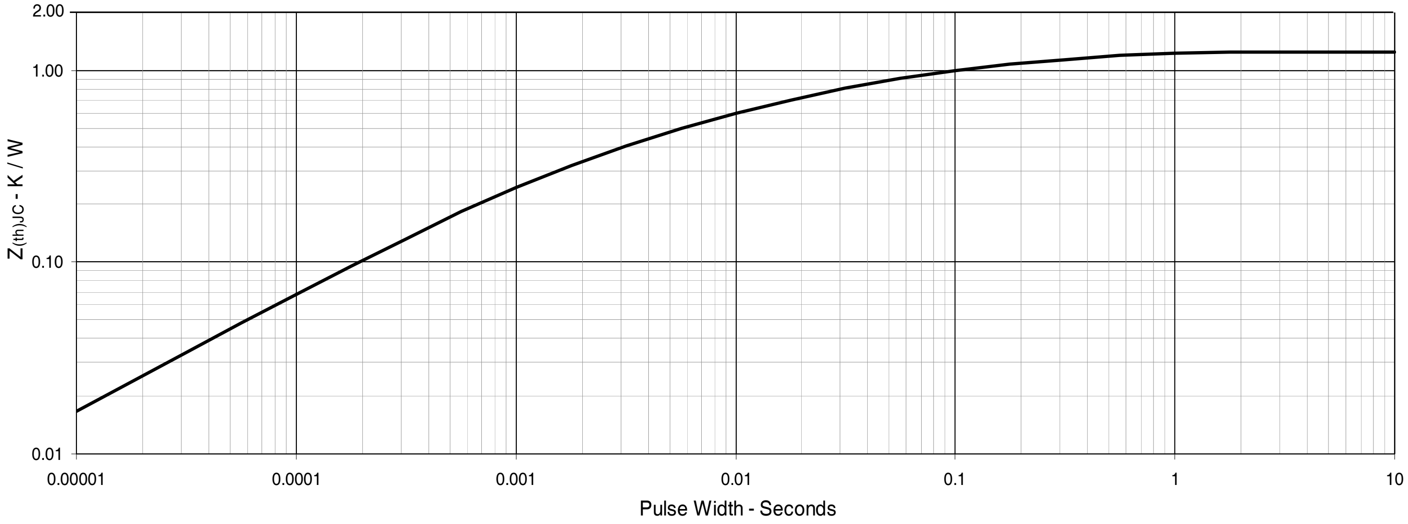
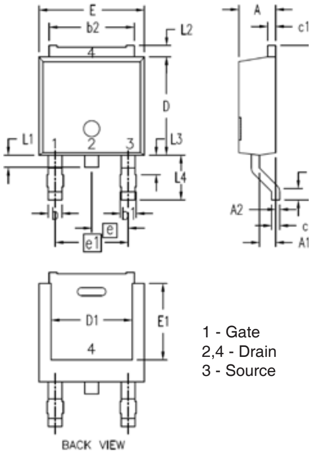


Fig. 17. Maximum Transient Thermal Resistance



IXYS REF: T_1R6N50D2 (2C-C15) 8-14-09

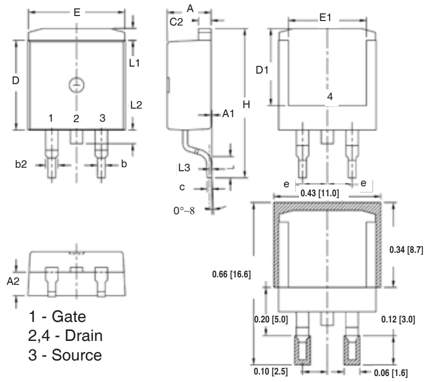
TO-252 Outline



1 - Gate
2,4 - Drain
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.086	.094	2.19	2.38
A1	.035	.045	0.89	1.14
A2	0	.004	0	0.10
b	.025	.035	0.64	0.89
b1	.030	.045	0.76	1.14
b2	.205	.215	5.21	5.46
c	.018	.023	0.46	0.58
c1	.018	.023	0.46	0.58
D	.235	.245	5.97	6.22
D1	.170	.205	4.32	5.21
E	.250	.265	6.35	6.73
E1	.170	.205	4.32	5.21
e	.090 BSC		2.28 BSC	
e1	.180 BSC		4.57 BSC	
H	.370	.410	9.40	10.42
L	.020	.040	0.51	1.02
L1	.025	.040	0.64	1.02
L2	.024	.036	0.60	0.90
L3	.045	.060	1.15	1.52
L4	.100	.115	2.54	2.92

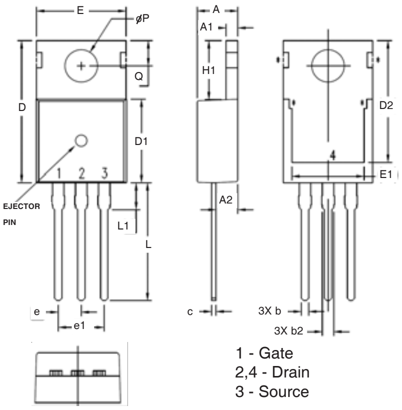
TO-263 Outline



1 - Gate
2,4 - Drain
3 - Source

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.060	1.18	1.52
C	.018	.024	0.45	0.60
C2	.049	.060	1.25	1.52
D	.340	.370	8.63	9.40
D1	.300	.327	7.62	8.30
E	.380	.410	9.65	10.41
E1	.270	.330	6.86	8.38
e	.100 BSC		2.54 BSC	
H	.580	.620	14.73	15.75
L	.075	.105	1.91	2.67
L1	.039	.060	1.00	1.52
L2	—	.070	—	1.77
L3	.010 BSC		0.254 BSC	

TO-220 Outline



1 - Gate
2,4 - Drain
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.047	.055	1.20	1.40
A2	.079	.106	2.00	2.70
b	.024	.039	0.60	1.00
b2	.045	.057	1.15	1.45
c	.014	.026	0.35	0.65
D	.587	.626	14.90	15.90
D1	.335	.370	8.50	9.40
(D2)	.500	.531	12.70	13.50
E	.382	.406	9.70	10.30
(E1)	.283	.323	7.20	8.20
e	.100 BSC		2.54 BSC	
e1	.200 BSC		5.08 BSC	
H1	.244	.268	6.20	6.80
L	.492	.547	12.50	13.90
L1	.110	.154	2.80	3.90
ØP	.134	.150	3.40	3.80
Q	.106	.126	2.70	3.20

IXYS

A Littelfuse Technology

EPlast1.ru

Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.

Как с нами связаться

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